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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	
2	T2	main terminal 2		T2
3	G	gate		sym051
mb	T2	mounting base; main terminal 2		symoor
			1 2 3	
			1 2 3	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT138-600D	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT138-600D	BT138-600D

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8. Limiting values

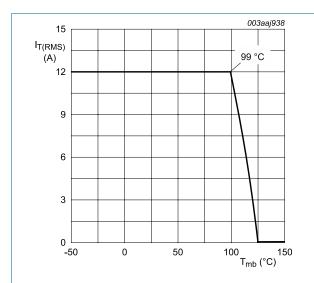
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; Fig 1; Fig 2; Fig 3	12	А
I _{TSM} non-repetitive peak on- state current		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; $Fig 4$; $Fig 5$	95	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	105	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	45	A ² s
dl _⊤ /dt	rate of rise of on-state	I _G = 10 mA; T2+ G+	50	A/µs
	current	I _G = 10 mA; T2+ G-	50	A/µs
		I _G = 10 mA; T2- G-	50	A/µs
		I _G = 20 mA; T2- G+	10	A/µs
I _{GM}	peak gate current		2	Α
P_GM	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		125	°C

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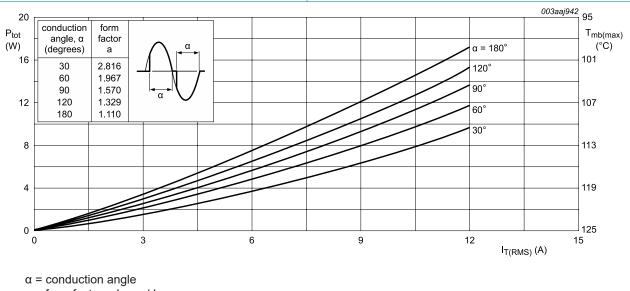
10 003aaj940 17(RMS) (A) 40 20 10 10-2 10-1 1 10 surge duration (s)

Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

2 RMS on-state current as a fu

 $f = 50 \text{ Hz}; T_{mb} = 99 ^{\circ}\text{C}$





a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

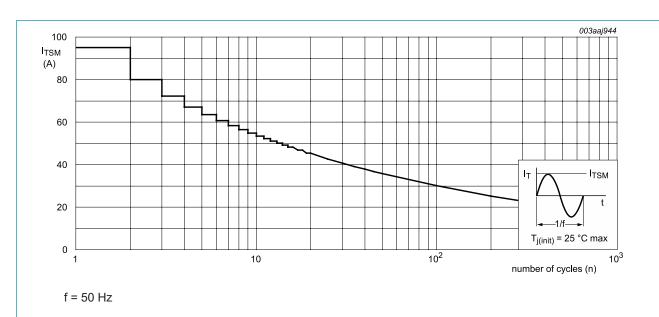


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum

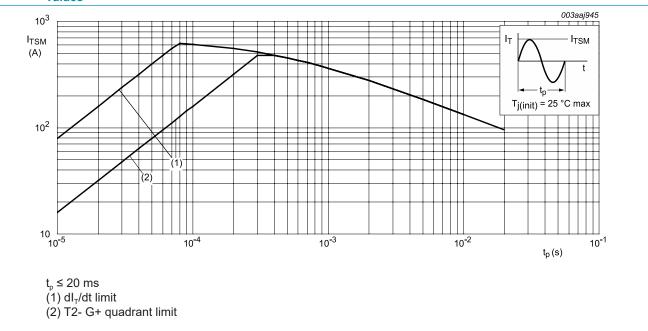


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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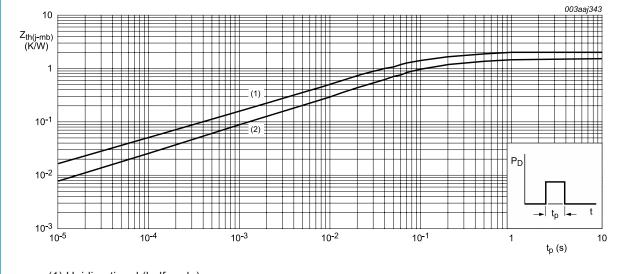
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; Fig 6	-	-	1.5	K/W
	from junction to mounting base	half cycle; <u>Fig 6</u>	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



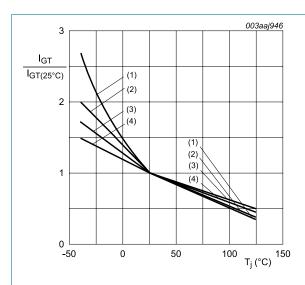
- (1) Unidirectional (half cycle)
- (2) Bidirectional (full cycle)

Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
l _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$ $T_j = 25 \text{ °C; } Fig. 7$	-	1.3	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	2.8	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G-;} $ $T_j = 25 \text{ °C; } \underline{\text{Fig. 7}}$	-	3.2	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G+;} $ $T_j = 25 \text{ °C; } Fig. 7$	-	5.5	10	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	15	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \overline{\text{Fig. 8}}$	-	-	15	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2- \text{ G+;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 8}}$	-	-	20	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	10	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.65	V
V _{GT} gate trigger voltage		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; gate open circuit	-	50	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 16 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

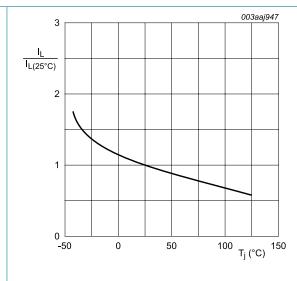


Fig. 8. Normalized latching current as a function of junction temperature

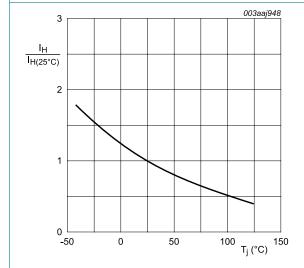
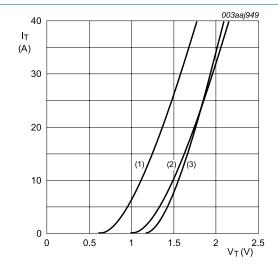


Fig. 9. Normalized holding current as a function of junction temperature



 V_o = 1.175 V; R_s = 0.0316 Ω

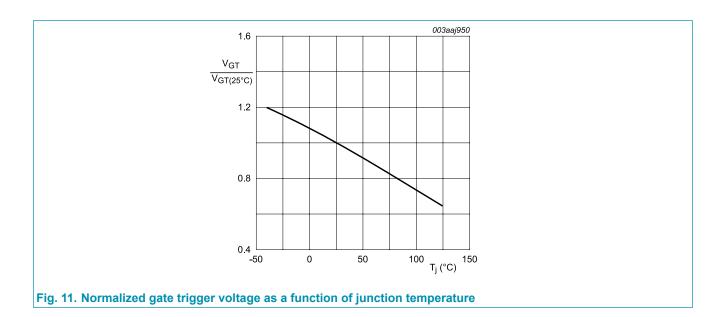
- (1) T_j = 125 °C; typical values (2) T_j = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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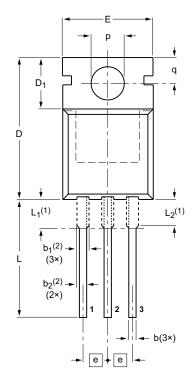


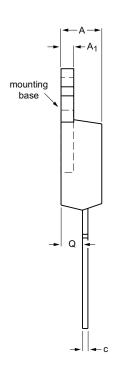
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11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







DIMENSIONS (mm are the original dimensions)

UNIT	А	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- $1. \ Lead \ shoulder \ designs \ may \ vary.$
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES		ISSUE DATE		
VERSION	IEC	JEDEC) JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13	

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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